2SB1412

Rev.E May.-2016

DATA SHEET

/ Descriptions

WR0585 Ṃ Ṃ Ŀ SQS Æ Ṁ ч s ǁ ˥ Silicon PNP transistor in a TO-252 Plastic Package.

/ Features

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Low $V_{CE(sat)}$,excellent DC current gain characteristics, complements the 2SD2118.

/ Applications

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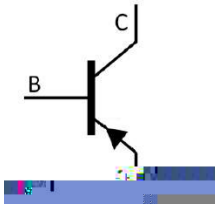
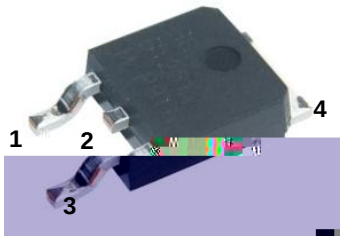
Medium power amplifier applications.

/ Equivalent Circuit



/ Pinning



PIN1 χ Base PIN 2,4 χ Collector PIN 3 χ Emitter

/ h_{FE} Classifications & Marking

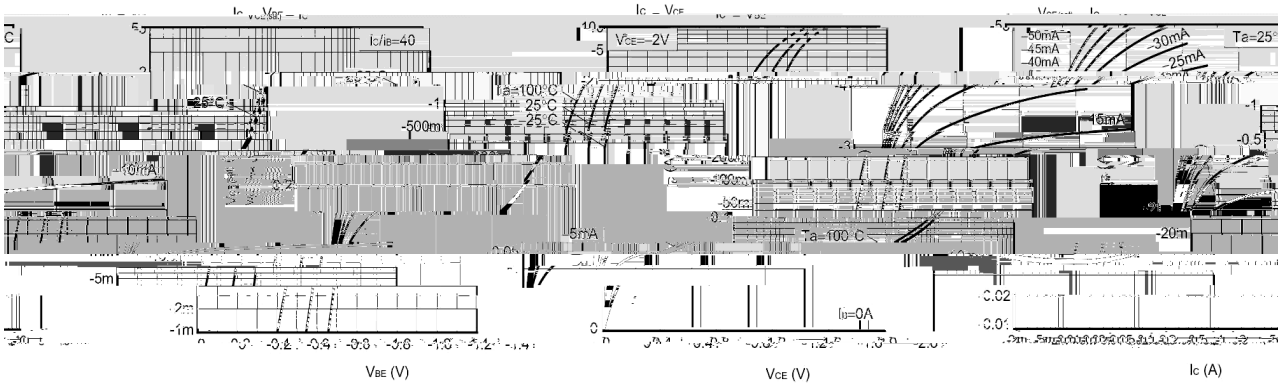
h_{FE} Classifications Symbol	P	Q	R
h_{FE} Range	82 180	120 270	180 390

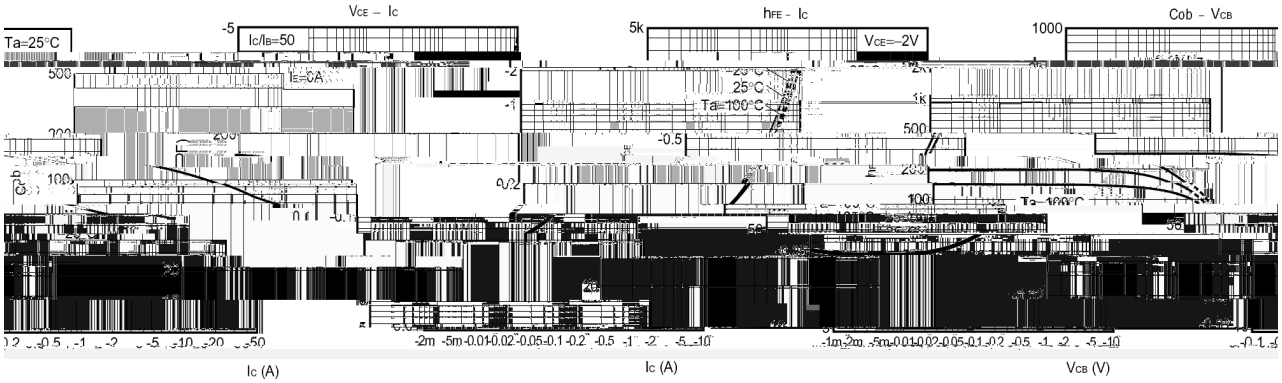
v ̈Ω Parameter	ϒ N Symbol	̈Ω Ö Rating	D Ӈ Unit
Collector to Base Voltage	V_{CBO}	-30	V
Collector to Emitter Voltage	V_{CEO}	-20	V
Emitter to Base Voltage	V_{EBO}	-6.0	V
Collector Current - Continuous	I_C	-5	A
Peak Collector Current – Continuous	I_{CM}	-10	A
Collector Power Dissipation	P_C	1.0	W
Collector Power Dissipation*	*P_C(Tc=25)	10	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

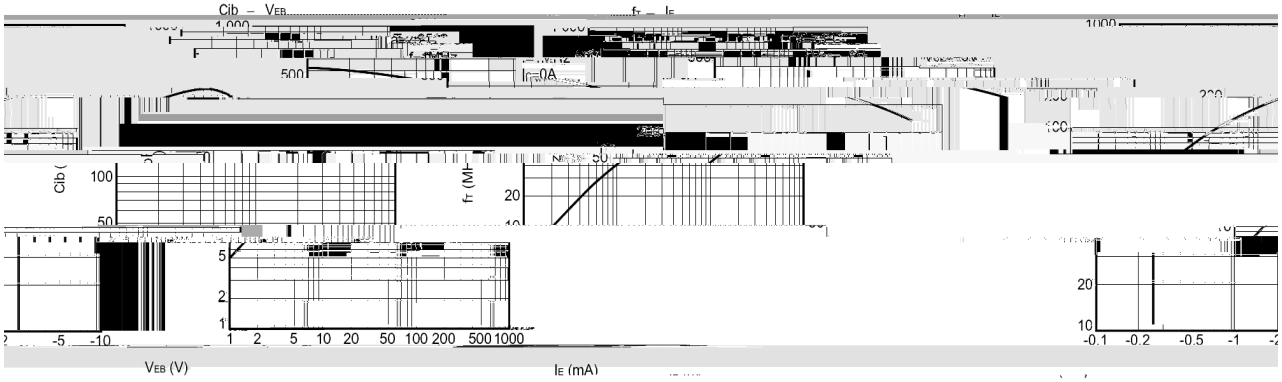
*mounted On40×40×0.7mm ceramic board.
-ᵒ Ɛ̂ ̂ 73Ö73Ö31: p p ⊞ ه — i

v ̈Ω Parameter	ϒ N Symbol	⊥⊥ ;ǀ Ţ Test Conditions	ω ṇ Ö Min	Ɛ ʒ Ö Typ	ω ᶻ Ö Max	D Ӈ Unit
Collector to Base Breakdown Voltage	V_{CBO}	I_C=-50μA I_E=0	-30			V
Collector to Emitter Breakdown Voltage	V_{CEO}	I_C=-1.0mA I_B=0	-20			V

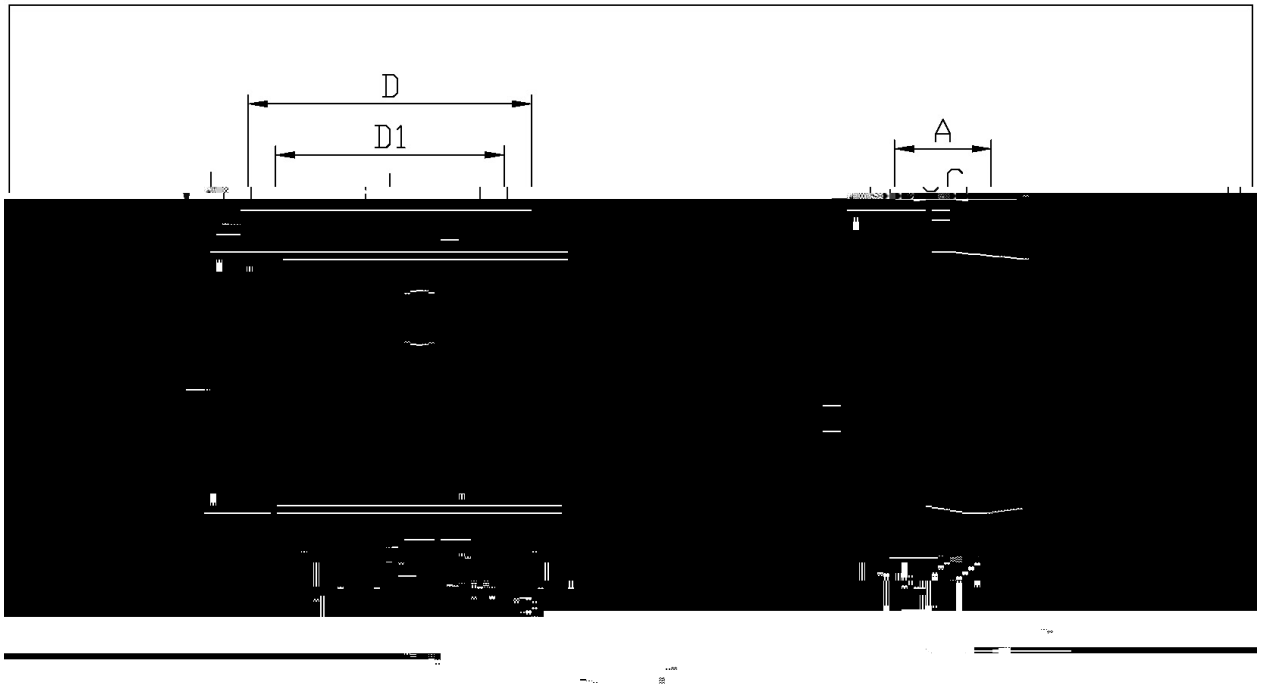
/ Electrical Characteristic Curve

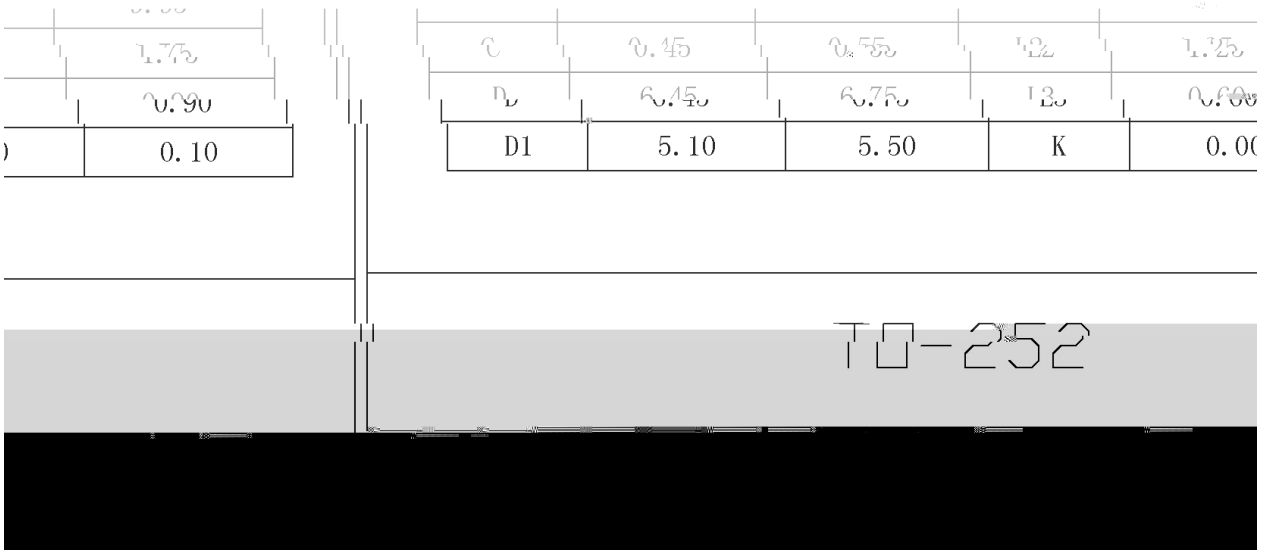




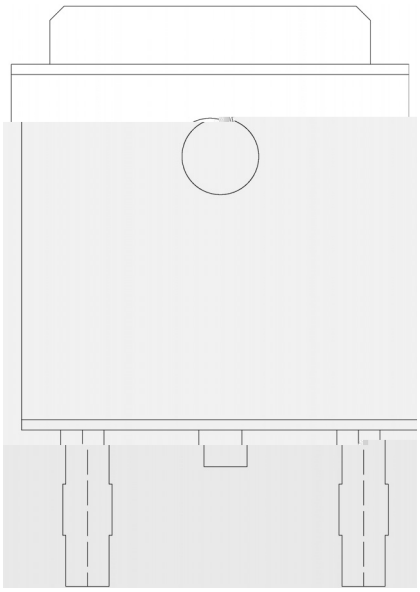


/ Package Dimensions





/ Marking Instructions



ب ˝ χ

BR χ	⌘ ⅋ ᴵ ⊓
E4745 χ	⌘ ⅋ ᴺ ⊓
S=	⌘ h_{FE} ‘ ⁶ ⊓
---- χ	⌘ ⅃ ⅎ ή ᴺ ⊓ ⅃ ⅋ ⅃ ⅎ ή ᴺ ψ ק

Note:

BR: Company C (Bde/AAking 174D([P:4.32737[2D0 Tc041e04b80556)Tj0941Tj/TTD(T4

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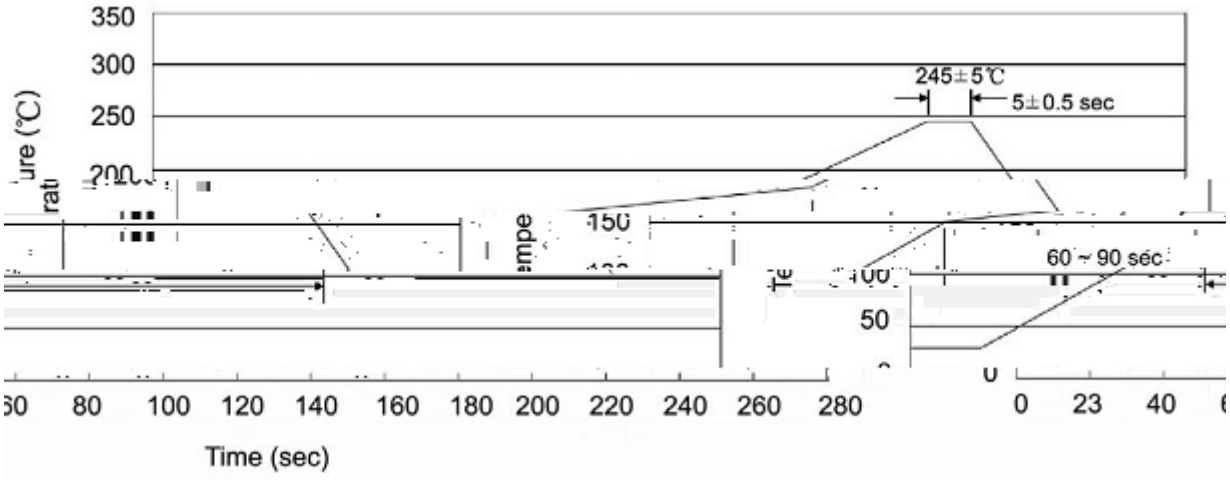

ب ˝ χ

1 أ ♬ □ ỷ 25 Ḱ 150 ł ı `H ڑ 60 Ḱ 90sec;

2 Š Ö □ ỷ 245 ° 5 ł ı `H ڑ ˙Y ⺈ ⺮ 5 ° 0.5sec;

3 ì ˙ ⺌ ˛ ɔ ھ ỷ ⺮ 2 Ḱ 10 ł /sec.

Note:

1.Preheating:25~150 ł , Time:60~90sec.

2.Peak Temp.:245 ° 5 ł , Duration:5 ° 0.5sec.

3. Cooling Speed: 2~10 ł /sec.

/ Resistance to Soldering Heat Test Conditions

□ ỷ χ 260 ° 5 ł `H ڑ χ 10 ° 1 sec. Temp.:260±5 Time:10±1 sec

/ Packaging SPEC.

ɔ` γ ŁΙ / REEL

Package Type	Units					Dimension		(unit mm^3)